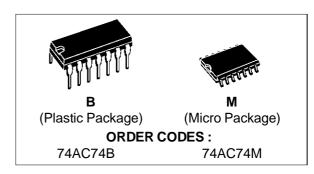


DUAL D-TYPE FLIP FLOP WITH PRESET AND CLEAR

- HIGH SPEED: f_{MAX} = 300 MHz (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: Icc = 4 µA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- 50Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 24 mA (MIN)
- BALANCED PROPAGATION DELAYS:
 tplh ≅ tphl
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 74
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The AC74 is an advanced high-speed CMOS OCTAL D-TYPE FLIP FLOP WITH PRESET AND CLEAR NON INVERTING fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.



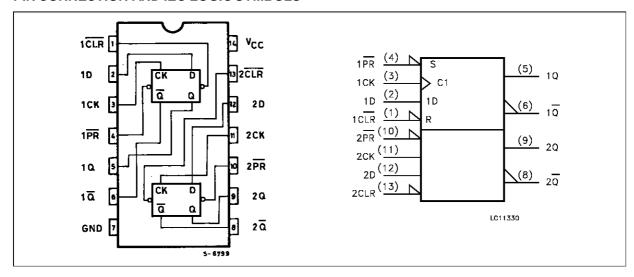
A signal on the D INPUT is transferred to the Q OUTPUT during the positive going transition of the clock pulse.

CLEAR and PRESET are independent of the clock and accomplished by a low setting on the appropriate input.

It is ideal for low power applications mantaining high speed operation similar to equivalent Bipolar Schottky TTL.

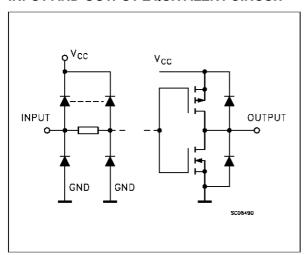
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



April 1997 1/11

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

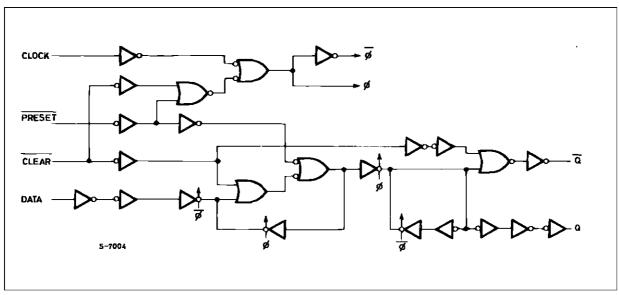
PIN No	SYMBOL	NAME AND FUNCTION
1, 13	1 <u>CLR,</u> 2CLR	Asyncronous Reset - Direct Input
2, 12	1D, 2D	Data Inputs
3, 11	1CK, 2CK	Clock Input (LOW-to-HIGH, Edge- Triggered)
4, 10	1PR, 2PR	Asyncronous Set - Direct Input
5, 9	1Q, 2Q	True Flip-Flop Outputs
6, 8	1\overline{Q}, 2\overline{Q}	Complement Flip-Flop Outputs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

TRUTH TABLE

	INPUTS			ОИТІ	PUTS	FUNCTION
CLR	PR	D	CK	Q	Q	
L	Н	Х	Х	L	Н	CLEAR
Н	L	Х	X	Н	L	PRESET
L	L	X	X	Н	Н	
Н	Н	L		L	Н	
Н	Н	Н		Н	L	
Н	Н	Х	- L	Qn	\overline{Q}_n	NO CHANGE

X: Don't Care

LOGIC DIAGRAMS



This logic diagram has not be used to estimate propagation delays



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to Vcc + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
lo	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 200	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	2 to 6	V
VI	Input Voltage	0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Rise and Fall Time V _{CC} = 3.0, 4.5 or 5.5 V(note 1)	8	ns/V

¹⁾ V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter Test (st Condi	Conditions		Value				
		Vcc			T _A = 25 °C			-40 to	85 °C	
		(V)			Min.	Тур.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	3.0	Vo=	0.1 V or	2.1	1.5		2.1		
		4.5	Vcc	c - 0.1 V	3.15	2.25		3.15		V
		5.5			3.85	2.75		3.85		
V_{IL}	Low Level Input Voltage	3.0		0.1 V or		1.5	0.9		0.9	
		4.5	Vcc	_c - 0.1 V		2.25	1.35		1.35	V
		5.5				2.75	1.65		1.65	
V_{OH}	High Level Output	3.0		Ιο=-50 μΑ	2.9	2.99		2.9		
	Voltage	4.5	V _I ^(*) =	I _O =-50 μA	4.4	4.49		4.4		
		5.5	V _{IH} or	I _O =-50 μA	5.4	5.49		5.4		V
		3.0	VIL	I _O =-12 mA	2.56			2.46		
		4.5		I _O =-24 mA	3.86			3.76		
		5.5		I _O =-24 mA	4.86			4.76		
V_{OL}	Low Level Output	3.0		I _O =50 μA		0.002	0.1		0.1	
	Voltage	4.5	V _I ^(*) =	I ₀ =50 μA		0.001	0.1		0.1	
		5.5	V _{IH} or	I _O =50 μA		0.001	0.1		0.1	V
		3.0	VIL	I _O =12 mA			0.36		0.44	
		4.5		I _O =24 mA			0.36		0.44	
		5.5		I _O =24 mA			0.36		0.44	
lı	Input Leakage Current	5.5	V _I = V _{CC} or GND				±0.1		±1	μΑ
I _{CC}	Quiescent Supply Current	5.5	V _I = V	_{CC} or GND			4		40	μΑ
I _{OLD}	Dynamic Output Current	5.5	V _{OLD} =	1.65 V max					75	mA
I _{OHD}	(note 1, 2)		V _{OHD} =	3.85 V min					-75	mA

¹⁾ Maximum test duration 2ms, one output loaded at time
2) Incident wave switching is guaranteed on transmission lines with impedances as low as 50 Ω.
(*) All outputs loaded.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}, R_L = 500 \Omega$, Input $t_r = t_f = 3 \text{ ns}$)

Symbol	Parameter	Te	st Condition	Value				Unit	
		V _{CC}		T _A = 25 °C		-40 to 85 °C			
		(V)		Min.	Тур.	Max.	Min.	Max.	
t _{PLH}	Propagation Delay Time	3.3 ^(*)			7	13		14	nc
t _{PHL}	CK to Q	5.0 ^(**)			5	10		11	ns
t _{PLH}	Propagation Delay Time	3.3 ^(*)			6	12		13	no
t_{PHL}	PR or CLR to Q	5.0 ^(**)			4.5	9		10 ns	115
t _w	Pulse Width HIGH or	3.3 ^(*)			1.5	5		7	no
	LOW, CK or PR or CLR	5.0 ^(**)			1.5	4		5	ns
ts	Setup Time D to CK	3.3 ^(*)			-0.2	4		4	
	HIGH or LOW	5.0 ^(**)			-0.2	3		3	ns
th	Hold Time D to CK	3.3 ^(*)			0.2	2		3	
	HIGH or LOW	5.0 ^(**)			0.2	2		3	ns
t _{REM}	Removal Time	3.3 ^(*)			-1	1		1	
	PR or CLR to CK	5.0 ^(**)			-0.7	1		1	ns
f _{MAX}	Maximum Clock	3.3 ^(*)		100	300		90		MHz
	Frequency	5.0 ^(**)		140	300		130		IVI Z

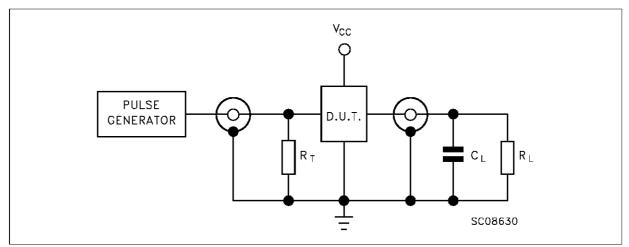
^(*) Voltage range is 3.3V ± 0.3V (**) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value					Unit
		Vcc		T _A = 25 °C		-40 to	85 °C		
		(V)		Min.	Тур.	Max.	Min.	Max.	
C _{IN}	Input Capacitance	5.0			4				рF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			35				pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$ (per circuit)

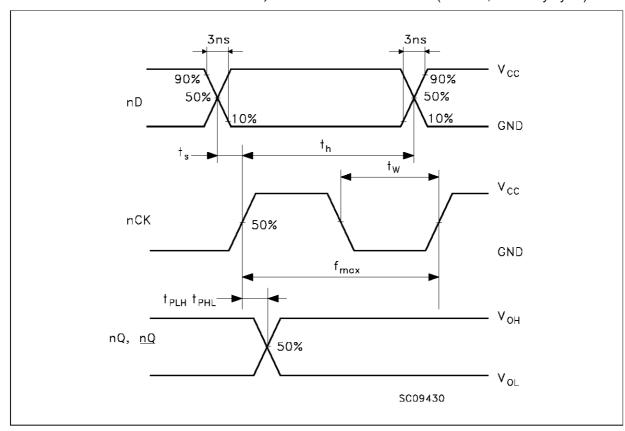
TEST CIRCUIT



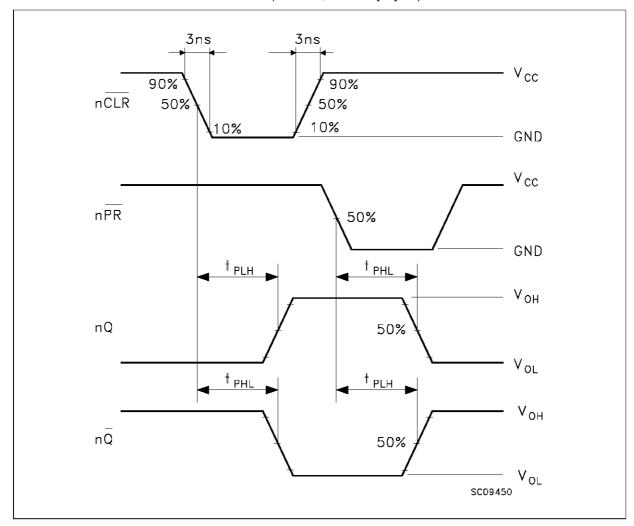
 C_L = 50 pF or equivalent (includes jig and probe capacitance) R_L = R_1 = 500Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

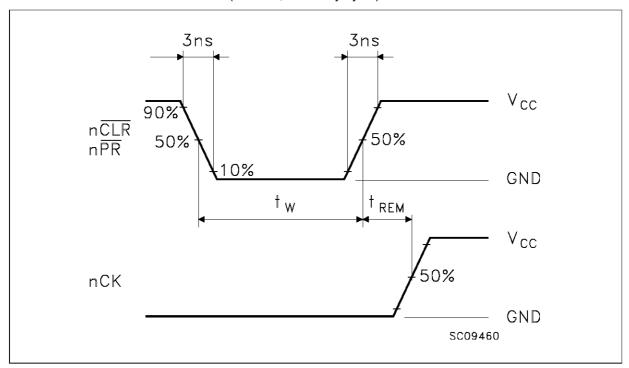
WAVEFORM 1: PROPAGATION DELAYS, SETUP AND HOLD TIMES (f=1MHz; 50% duty cycle)



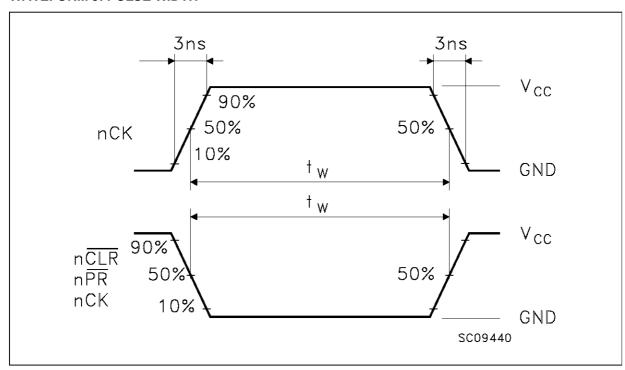
WAVEFORM 2: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



WAVEFORM 3: RECOVERY TIMES (f=1MHz; 50% duty cycle)

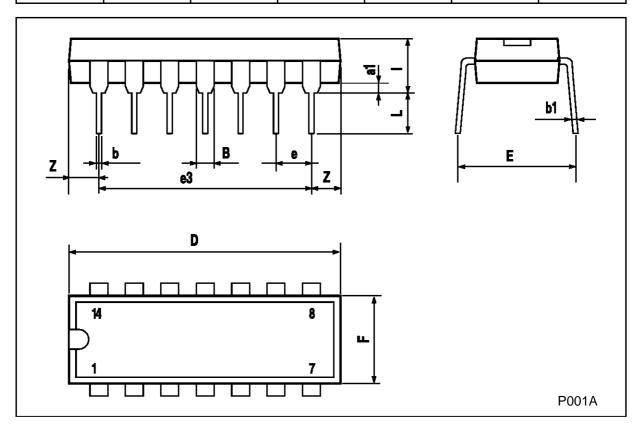


WAVEFORM 3: PULSE WIDTH



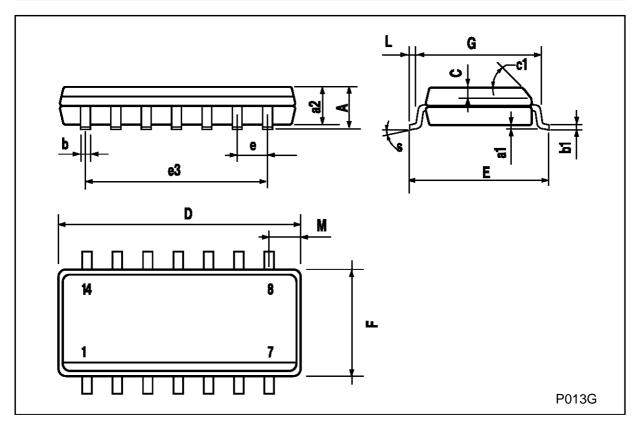
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch				
5.W.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
Е		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



SO14 MECHANICAL DATA

DIM.		mm		inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45	(typ.)			
D	8.55		8.75	0.336		0.344	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		7.62			0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8 (r	max.)			



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